



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Wenge Yang

Serial No. : 09/805,273

Group Art Unit: 2823

Filed : 03/13/2001

Examiner: ESTRADA, M.

Title : HIGHLY CONDUCTIVE SEMICONDUCTOR STRUCTURES,
METHOD OF FORMING SAME VIA PLASMA ETCH, AND
ELECTRICAL DEVICES INCORPORATING HIGHLY
CONDUCTIVE SEMICONDUCTOR STRUCTURES

AMENDMENT AND RESPONSE AFTER FINAL ACTION

Mail Stop AF
Commissioner for Patents
P.O Box 1450
Alexandria, VA 22313-1450

Sir:

In response to the Final Office Action mailed 06/14/2005, please enter and consider the following amendments, remarks and arguments for the above captioned patent application.

Amendments to the Claims are reflected in the listing of claims, which begins on page 2 of this paper.

Remarks/Arguments begin on page 9 of this paper.

ENTERED
BY
RCE
9/8/05
VS

CONCLUSION

It is respectfully submitted that the above claims, arguments and remarks overcome all rejections and objections. All remaining claims (Claims 35-55) are neither anticipated nor obvious in view of the cited references. For at least the above-presented reasons, it is respectfully submitted that all remaining claims (Claims 35-55) are in condition for allowance.

The Examiner is urged to contact Applicant's undersigned representative if the Examiner believes such action would expedite resolution of the present Application.

Please charge any additional fees or apply any credits to our PTO deposit account number: 23-0085.

Respectfully submitted,

WAGNER, MURABITO & HAO, LLP

Dated: _____

8/12/2005

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Attachment

IN RE DANIEL S. FULTON and JAMES HUANG, 04-1267 (Fed. Cir. 2004)